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FEATURES

Collector Current Capability $I_C=20\text{mA}$

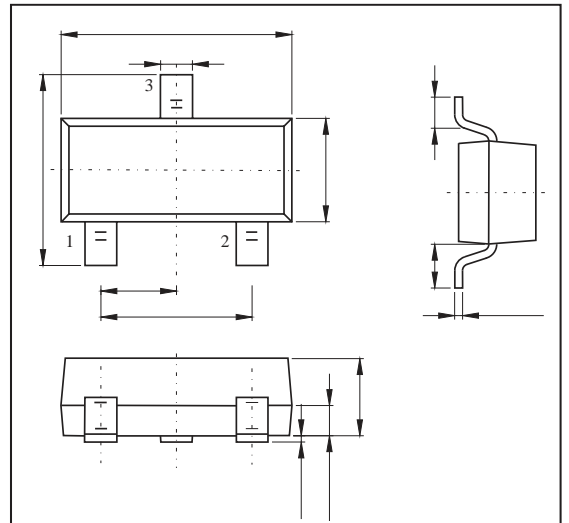
Collector Emitter Voltage $V_{CE0}=30\text{V}$

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Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	40	V
Collector - Emitter Voltage	V_{CEO}	30	
Emitter - Base Voltage	V_{EBO}	4	
Collector Current - Continuous	I_C	20	mA
Collector Power Dissipation	P_C	100	mW
Thermal Resistance from Junction to Ambient	R_{JA}	1000	/W
Junction Temperature	T_J	125	
Storage Temperature Range	T_{stg}	-55 to +125	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C=100\mu A, I_E=0$	40			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C=1\text{ mA}, I_B=0$	30			
Emitter - base breakdown voltage	V_{EBO}	$I_E=100\text{ A}, I_C=0$	4			
Collector-base cut-off current	I_{CBO}	$V_{CB}=18\text{ V}, I_E=0$			0.5	uA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{ V}, I_C=0$			0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{ mA}, I_B=10\text{mA}$			0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{ mA}, I_B=10\text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE}=6\text{ V}, I_C=1\text{ mA}$	40		200	
Noise Figure	NF	$V_{CE}=6\text{ V}, I_E=-1\text{ mA}, f=100\text{MHz}$		2.5	5	dB
Reverse Transfer capacitance	C_{re}	$V_{CB}=6\text{ V}, I_E=0, f=1\text{MHz}$		0.7		pF
Transition frequency	f_T	$V_{CE}=6\text{ V}, I_C=1\text{ mA}$		550		MHz

